

SPUTTERING TARGET AND METHOD FOR MANUFACTURING SAME

ABSTRACT OF THE DISCLOSURE

Provided are a target capable of suppressing cracks in the target and suitable for forming, for example, a soft magnetic film of a heat-assisted magnetic recording medium, and a method for manufacturing the target. In a sputtering target having a composition formula expressed as $\text{Fe}_{100-a-b-c}\text{-Cu}_a\text{-Si}_b\text{-M}_c$ in terms of atomic ratio, wherein $0.1 \leq a \leq 5.0$, $10.0 \leq b \leq 20.0$, $10.0 \leq c \leq 25.0$, and M is one or more elements selected from Nb and B, containing a remainder composed of unavoidable impurities, and having a bending strength of 500 MPa or more, a number of Fe phases having an inscribed circle diameter of 1 μm or greater is preferably less than 1.0 per 60000 μm^2 .

FIG. 1